



30V PNP LOW SATURATION MEDIUM POWER TRANSISTOR

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications.

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.05 grams (Approximate)

Features

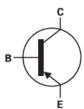
- BV_{CEO} > -30V
- I_C = -5.5A Continuous Collector Current
- I_{CM} = -20A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -60mV Max @ -1A
- $R_{SAT} = 24m\Omega$ @ -5.5A for Low Equivalent On-Resistance
- Exceptional Gain Linearity Down to -10mA
- h_{FE} Specified up to -20A for High Gain Hold Up
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Applications

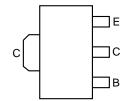
- DC-DC Converters
- MOSFET Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control



Top View



Device Schematic



Pin-Out Top View

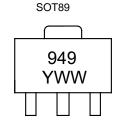
Ordering Information (Notes 4 and 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP2008ZQTA	949	7	12	1000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



949 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 8 = 2018) WW = Week code (01 - 53)



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5.5	A
Peak Pulse Current	I _{CM}	-20	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	6	1.5 12	W
Linear Derating Factor	(Note 7)	P_{D}	2.1 16.8	mW/°C
Thermal Resistance, Junction to Ambient	(Note 6)	R _{OJA}	83	
mermai Resistance, Junction to Ambient	(Note 7)	$R_{\Theta JA}$	60	°C/W
Thermal Resistance, Junction to Lead	(Note 8)	ReJL	3.23	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

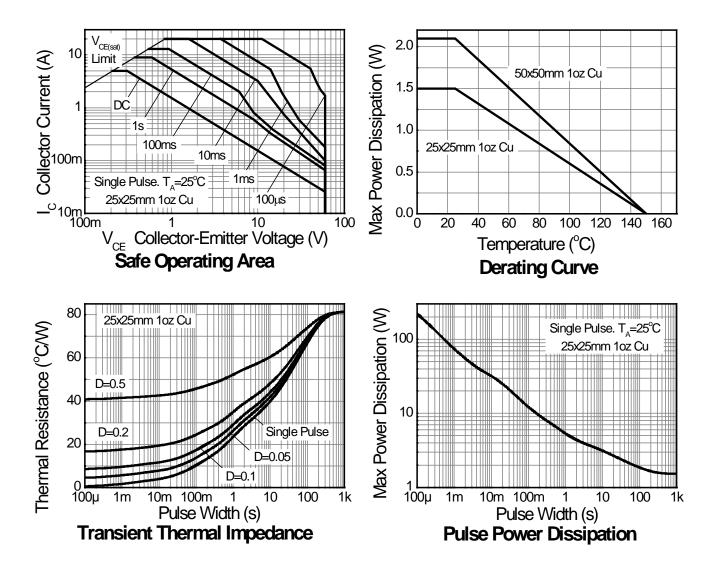
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions while operating in steady-state.
- 7. Same as Note 5, except the device is mounted on 50mm × 50mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

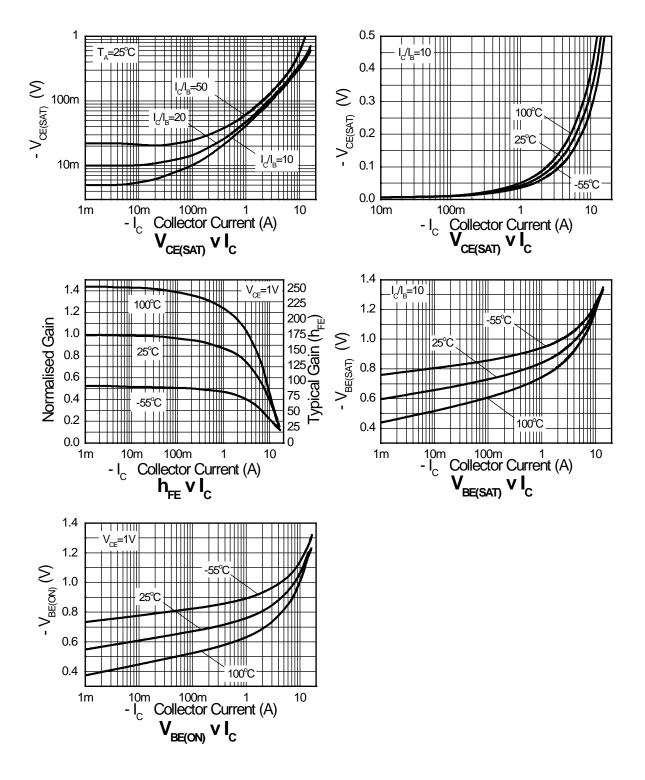
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	-70	_	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	-50	-70	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-30	-40	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8	_	V	$I_E = -100 \mu A$
Collector Cutoff Current	I _{CBO}	_	< -1 —	-20 -0.5	nΑ μΑ	V _{CB} = -40V V _{CB} = -40V, T _A = +100°C
Collector Cutoff Current	I _{CER}	_	< -1 —	-20 -0.5	nΑ μΑ	$V_{CB} = -40V$, $T_A = +100$ C $V_{CB} = -40V$, $R \le 1kΩ$ $V_{CB} = -40V$, $T_A = +100$ °C, $R \le 1kΩ$
Emitter Cutoff Current	I _{EBO}	_	< -1	-10	nA	V _{EB} = -6V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}	_	-25 -35 -55 -55 -130	-40 -55 -80 -80 -175	mV	$I_C = -0.5A$, $I_B = -20mA$ $I_C = -1A$, $I_B = -100mA$ $I_C = -1A$, $I_B = -20mA$ $I_C = -2A$, $I_B = -200mA$ $I_C = -5.5A$, $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(SAT)}	_	-970	-1070	mV	I _C = -5.5A, I _B = -500mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	_	-860	-960	mV	I _C = -5.5A, V _{CE} = -1V
DC Current Gain (Note 10)	h _{FE}	100 100 70 10	225 200 145 20	300		I _C = -10mA, V _{CE} = -1V I _C = -1A, V _{CE} = -1V I _C = -5A, V _{CE} = -1V I _C = -20A, V _{CE} = -1V
Transition Frequency	f _T	_	110		MHz	V _{CE} = -10V, I _C = -100mA, f = 50MHz
Output Capacitance (Note 10)	C _{OBO}	_	83	Ė	pF	V _{CB} = -10V, f = 1MHz
Switching Times	t _{ON}		43 230		ns	V _{CC} = -10V, I _C = -1A, I _{B1} = -I _{B2} = 100mA

Note:

10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



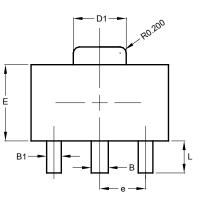
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

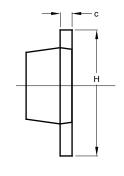




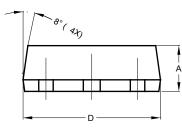
Package Outline Dimensions

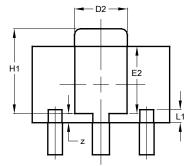
Please see http://www.diodes.com/package-outlines.html for the latest version.





SOT89

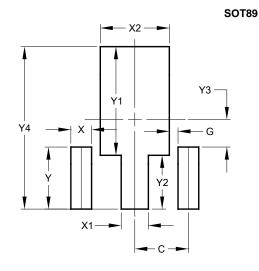




SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
Н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
Z	0.20	0.40	0.30			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value		
Dilliensions	(in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
V۵	4 530		



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